

BACK-END

MOS-FET

IGBT

THYRISTOR

DIODE

ZENER DIODE

SEMICONDUCTOR TEST SYSTEM 半導体テストシステム

CHTDV3010ZZ 3000V
1000A

NEW

- CHTDV3010ZZ has forcing ability of 3000V/1000A for DC measurement, 300A for thermal resistance measurement, which is better forcing ability than CHTDV1030Z. This tester has the scanner function of 30 pins to measure multi-element device.
- CHTDV3010ZZはDC測定の印加能力が3000V/1000A、熱抵抗測定の印加能力が300Aと、CHTDV1030Zよりも大きな印加能力を持っています。また30ピンのスキャナ機能を持ち、多素子のデバイス測定にも対応しています。



MODEL	CHTDV3010ZZ
SOFTWARE	
TEST PLAN/SORT PLAN	1000/1000
BIN OUT	24
DC TEST	
MEASURABLE DEVICES	N MOS-FET, N-IGBT, N-THYRISTOR, N-DIODE
VOLTAGE/CURRENT	1000V/10A (High voltage/High current : 3kV/1000A)
THERMAL RESISTANCE TEST	
CURRENT	300A
TEST ITEMS (High voltage/High current)	
MOS-FET	HIDs, HBVDs, HVFSDs, HVGstH, HVTH, HVdSON, HRdSON, HLVdSON, HLRdSON, HIdON, HGMP
IGBT	HICE, HBVCE, HVFECS, HVGEth, HVTH, HVCEON, HICON, HGMP
THYRISTOR	HIDRM, HIRGM, HVRGM, HVTM, HVDRM
DIODE	HIR, HVR, HVF
ZENER DIODE	HIZ, HVZ, HVF, ZZ, RZ
DIMENSIONS & WEIGHT	
MAIN UNIT A	550(W)+860(D)×1700(H)…345kg
MAIN UNIT B	550(W)+860(D)×1700(H)…275kg